DESCRIPTION

The BCX56, BCX56-10L, BCX56-16L are available in SOT89-3 package.

ORDERING INFORMATION

Package Type	Part Number	
SOT89-3	BCX56	
	BCX56-10L	
	BCX56-16L	
Note	SPQ: 1,000pcs/Reel	
AiT provides all RoHS Compliant Products		

Range	BCX56	BCX56-10L	BCX56-16L
h _{FE}	63~250	63~160	100~250

FEATURE

- High current (max. 1A)
- Low voltage (max. 80V)
- NPN Transistors

APPLICATIONS

Driver stages of audio and video amplifiers

PIN DESCRIPTION



Pin#	
1	BASE
2	COLLECTOR
3	EMITTER

ABSOLUTE MAXIMUM RATINGS

V _{CEO} , Collector-Emitter Voltage	80V
V _{CBO} , Collector-Base Voltage	100V
V _{EBO} , Emitter-Base Voltage	5V
I _C , Collector Current (DC)	1A
Icm, Peak Collector Current	1.5A
I _{вм} , Peak Base Current	0.2A
Pc, Collector Power Dissipation	0.5W
T _J , Junction Temperature	150°C
T _{STG} , Storage Temperature Range	-55°C ~+150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: Device mounted on a printed-circuit board, single sided copper, tinplated, mounting pad for collector 6cm2.

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ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified.

Parameter	Symbol	Conditions	Min	Тур.	Max	Unit
Collector Cut-Off Current	Ісво	V _{CB} =30V, I _E =0	-	-	100	nA
		V _{CB} =30V, I _E =0		-	10	μА
		T _J =150°C	-			
Emitter Cut-Off Current	I _{EBO}	V _{EB} =5V, I _C =0	-	-	100	nA
DC Current Gain	h _{FE}	V _{CE} =2V, I _C =5mA	63	-	-	-
		V _{CE} =2V, I _C =150mA	63	-	250	
		V _{CE} =2V, I _C =500mA	40	-	-	
Collector-Emitter	V _{CE(sat)}	I _C =500mA, I _B =50mA,		-	0.5	V
Saturation Voltage			-			
Base-Emitter Voltage	V_{BE}	I _C =500mA, V _{CE} =2V	-	-	1	V
Transition Frequency	f⊤	I _C =10mA, V _{CE} =5V		130		NALI-
		f=100MHz	_			MHz

TYPICAL PERFORMANCE CHARACTERISTICS

Fig 1. Static Characteristic

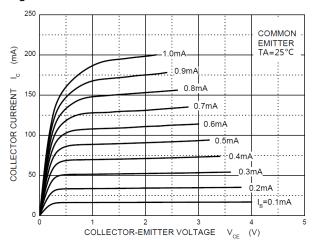
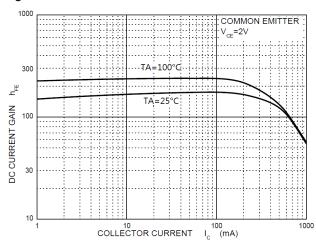
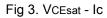


Fig 2. hfe - lc



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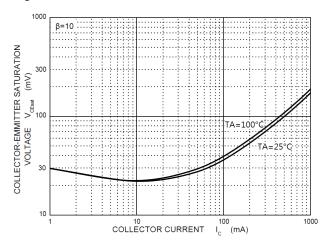


Fig 4. VBEsat - Ic

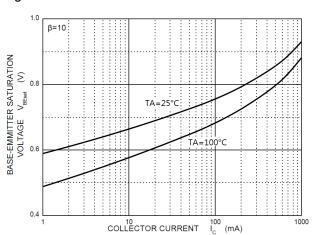


Fig 5. Ic - V_{BE}

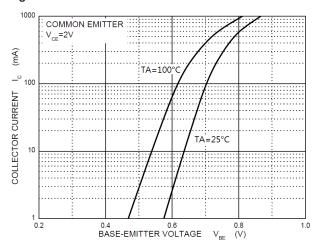


Fig 6. Cob/Cib - VcB/VEB

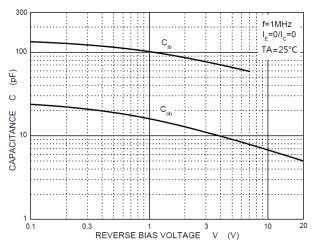


Fig 7. f_T - Ic

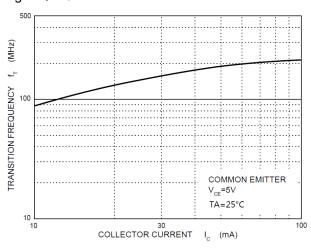
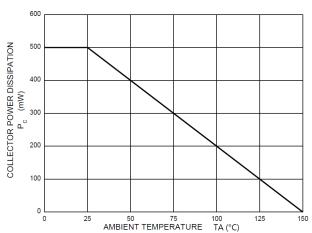


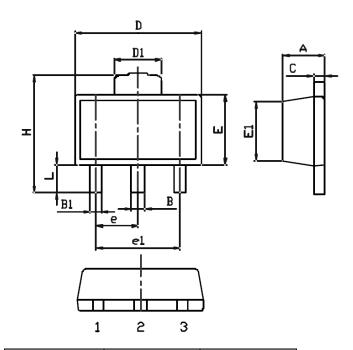
Fig 8. Pc - TA



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PACKAGE INFORMATION

Dimension in SOT89-3 (Unit: mm)



Symbol	Min.	Max.	
Α	1.40	1.60	
В	0.46	0.56	
B1	0.36	0.48	
С	0.35	0.44	
D	4.40	4.60	
D1	1.62	1.83	
E	2.29	2.60	
E1	2.29	2.60	
е	1.50 REF		
e1	3.00 REF		
Н	3.94	4.25	
L	0.89	1.20	





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